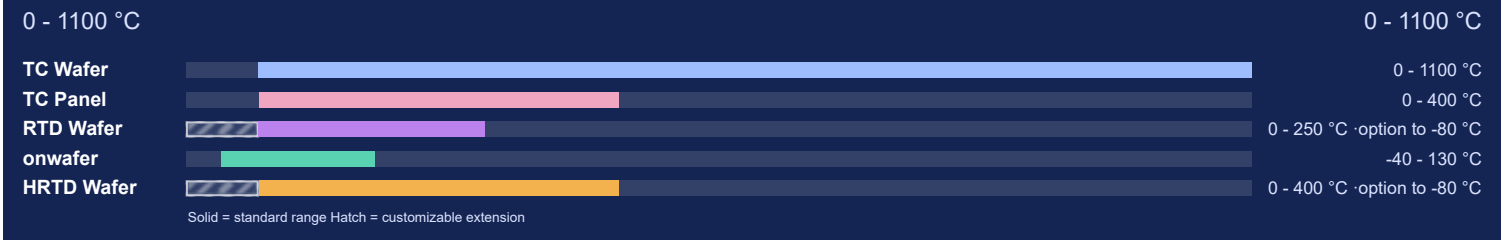
WAFER LEVEL THERMAL METROLOGY

Thin Films and Thermal Processes

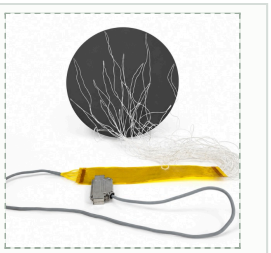
THERMAL/WAFE

Product specification brief

PROCESS WINDOWS / SENSOR CONFIGURATION / FIELD VALIDATION



Product portfolio



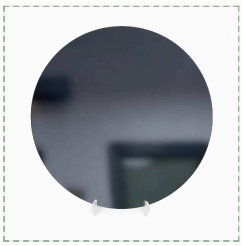
TC Wafer
TCW-K · ±1.1 °C / 0.4%
wired



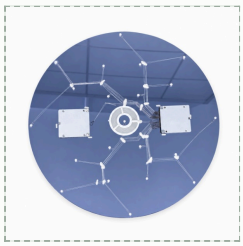
TC Panel
TCP · ±1.1 °C / 0.4%
wired



RTD Wafer
RTDWafer · ±0.05 °C
wired



onwafer
onwafer · ±0.1 °C
Wireless



HRTD Wafer
HRTD Wafer · ±1 °C
Wireless

Product specifications

Parameter	Unit / basis	TC Wafer	TC Panel	RTD Wafer	onwafer	HRTD Wafer
Product name / model		TCW-K	TCP	RTDWafer	onwafer	HRTD Wafer
Accuracy	± °C	1.1°C / 0.4%	±1.1 °C	0.05	0.1	1
Resolution	°C	0.1	0.1	0.001	0.01	0.1
Sensor to sensor	< °C	0.2	0.2	0.03	0.1	0.6
Sensor type		Type-K	Type-K	RTD	IC	RTD
Standard points	num	1-5-9-13-17-21	10-17	1-5-9-13-17-21	53-65	9-13-17-21
Power		External	External	External	Battery	Battery
Notes		Commercial	Commercial	Wired wafer	Wireless wafer, plasma compatible	Wireless wafer, plasma incompatible

Parameter	Unit / basis	TC Wafer	TC Panel	RTD Wafer	onwafer	HRTD Wafer
Max sampling rate	Hz	1 - 10 Hz	1 - 10 Hz	1 - 10 Hz	1 - 2 Hz	1 - 2 Hz
Operating range	Min - max °C	0 °C - 1100 °C	0 °C - 400 °C	0 °C - 250 °C	-40 °C - 130 °C	0 °C - 400 °C
Calibration range	Min - max °C	NA	NA	RT - 240 °C	-20 °C - 110 °C	RT - 350 °C
Substrate		Silicon / silicon carbide / sapphire	Silicon / glass	Silicon	Silicon	Silicon
Wafer size	mm	25 - 300	25 - 300	150 - 300	150 - 300	200 - 300
Wire diameter	mm	0.127	0.127	FPC	NA	NA
Product weight	g	NA	NA	NA	12 inch - 190 g / 8 inch - 120 g	12 inch - 200 g / 8 inch - 130 g
Top coating		NA	NA	NA	Yttrium oxide / others	NA
Power system		external PSU	external PSU	external PSU	Wireless charging	Wireless charging
Communication		mini plug	mini plug	D-SUB	bluetooth	bluetooth
Thickness	mm above	NA	NA	NA	1.16	8
Charge time	min	NA	NA	NA	30	30
Record time	min	Unlimited	Unlimited	Unlimited	80 (RT)	80 (RT)
Operation hours	hours	NA	NA	NA	6 h	6 h
Certify interval period	months	NA	NA	12	12	12